A	2022.2.12	ALL	AOS-AOD294A		

TO-252 N

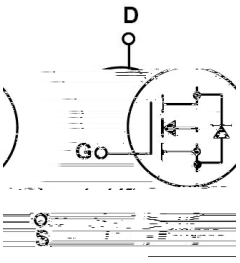
N-CHANNEL MOSFET in a TO-252 Plastic Package.

$R_{DS(on)}$ C_{rss}

Low $R_{DS(on)}$,low gate charge, low C_{rss}, fast switching, HF Product.

DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.





PIN1 G PIN 2 D PIN 3 S PIN 4 D

See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Drain Current		I_D(Tc=25℃)	55	A
Drain Current - Pulsed		I_{DM}	138	A
Gate-Source Voltage		V_{GS}	±20	V
Avalanche Current		I_{AS}	7.0	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	24.5	mJ
Power Dissipation		P_D(Tc=25℃)	73	W
Storage Temperature Range		T_{stg}	-55 to 150	℃
Thermal Resistance-Junction to Ambient	t≤10s	$R_{\theta JA}$	20	℃/W
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.7	

DS

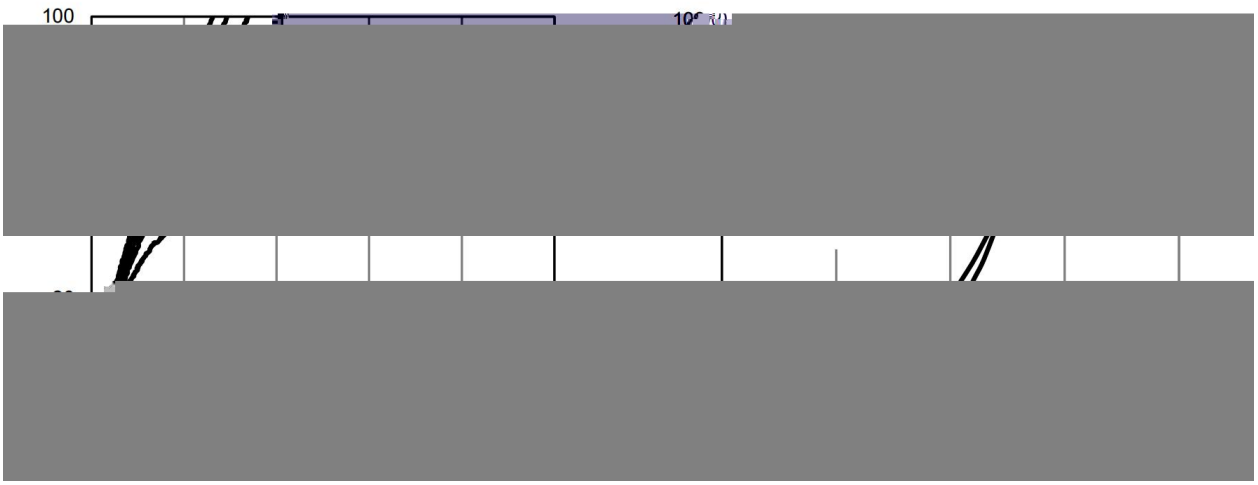
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	108		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V V_{GS}=0V			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	1.5	1.8	2.5	V

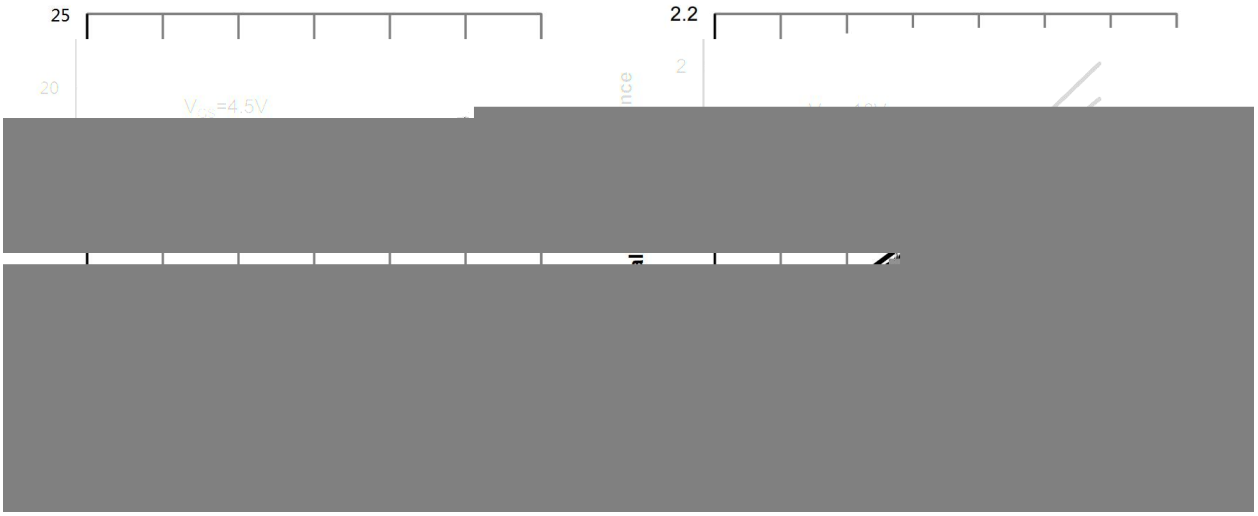
Static Drain-Source
On-

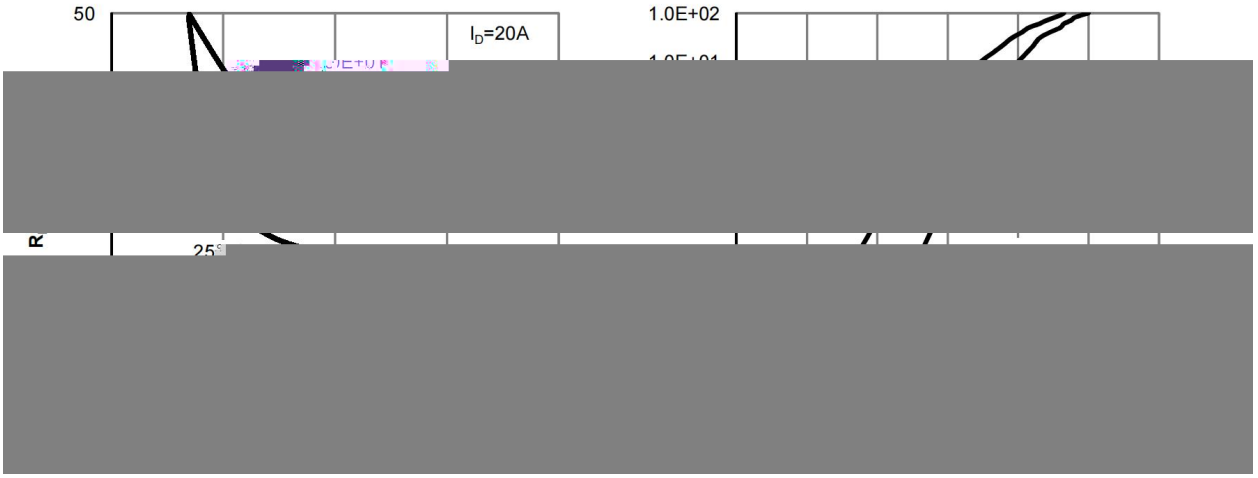
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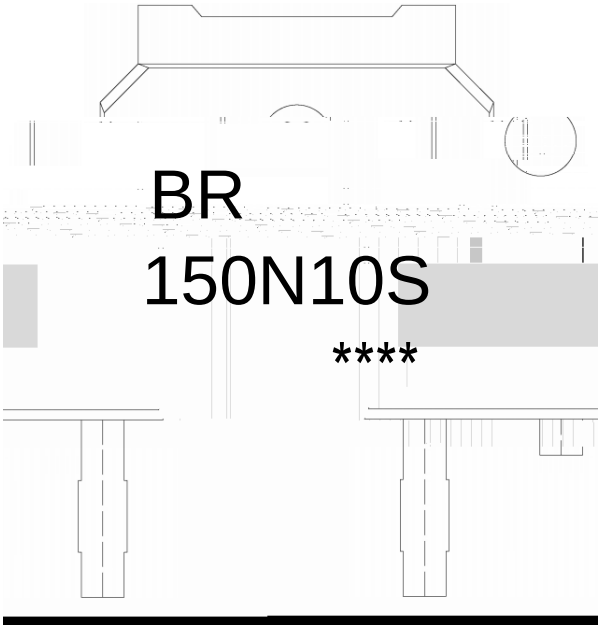
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Rev.A Feb.-2022


100


25
20
2.2
2


50
I_D=20A
1.0E+02



BR

150N10S

****

Note:

BR:	Company Code
150N10S:	Product Type Code
****:	Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)



				Note:
1	150	180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5		5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2 10	/sec.	3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ REEL

Package Type Units Dimension (unit mm